

PATENT CLAIMS

5 1. Etching solutions comprising hydrofluoric acid, an organic solvent, individually or as a mixture selected from the group consisting of ethylene glycol, propylene glycol, ethanol and glycerol, and water for the production of integrated circuits.

10 2. Etching solutions according to Claim 1, comprising 5 - 20% by weight of hydrofluoric acid.

15 3. Etching solutions according to Claim 1, comprising an organic solvent selected from the group consisting of ethylene glycol, propylene glycol, ethanol and glycerol.

20 4. Etching solutions according to Claim 1, comprising, as organic solvent, ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.

25 5. Etching solutions according to Claim 1, comprising, as organic solvent, ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.

30 6. Etching solutions according to Claims 1 to 5, comprising water in an amount of from 1 to 20% by weight.

35 7. Etching solutions according to Claims 1 to 6, comprising a mixture of high-purity individual components.

8. Use of the etching solutions according to Claims 1 to 6 for the selective etching of doped silicate layers.

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